

9097250 TOSHIBA (DISCRETE/OPTO)

67C 09314 DT-01-09

Silicon Planar Type

Diode

1S2460~1S2462

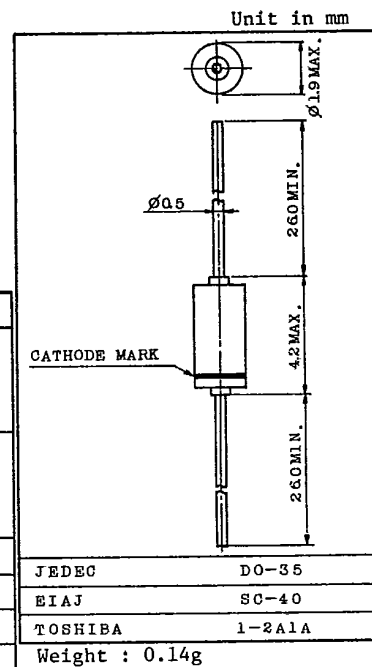
GENERAL PURPOSE RECTIFIER APPLICATIONS.

FEATURES:

- . High Reverse Voltage : $V_R=200V(\text{Min.})$ (1S2462)
- . Low Forward Voltage : $V_F=1.0V(\text{Max.})$
- . Hermetically Sealed Miniature Glass Package.

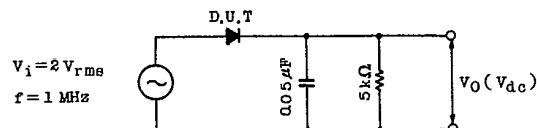
MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	1S2460	70	V
	1S2461	120	
	1S2462	220	
Reverse Voltage	1S2460	50	V
	1S2461	100	
	1S2462	200	
Maximum (Peak) Forward Current	I_{FM}	300	mA
Average Forward Current	I_O	100	mA
Surge Current (1 sec)	I_{FSM}	800	mA
Power Dissipation	P	250	mW
Junction Temperature	T_j	175	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 ~ 175	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F	$I_F=100\text{mA}$	-	0.9	1.0	V
Reverse Current	I_R	$V_R=50V$	-	-	1.2	μA
		$V_R=100V$				
		$V_R=200V$				
Rectification Efficiency	η	$f=1\text{MHz}, V_i=2V_{rms}$ (Fig.)	35	-	-	%
Total Capacitance	CT	$V_R=0, f=1\text{MHz}$	-	5	10	pF

Fig. : TEST CIRCUIT



$$\eta = \frac{V_O(V_{dc})}{\sqrt{2} \times V_i(V_{rms})}$$

$$= 353 \times V_O(V_{dc})(\%)$$

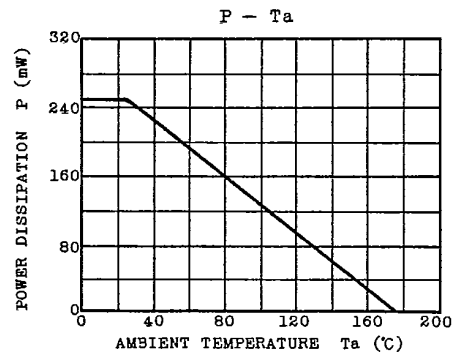
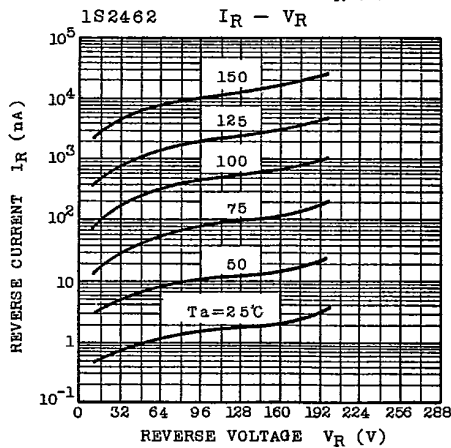
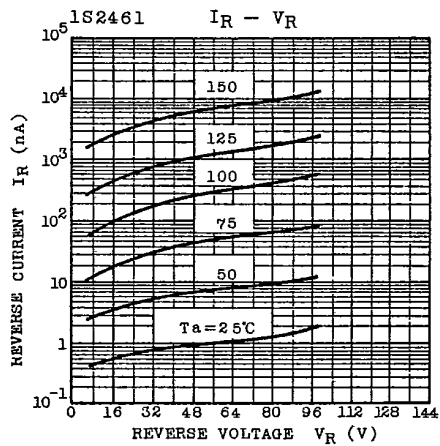
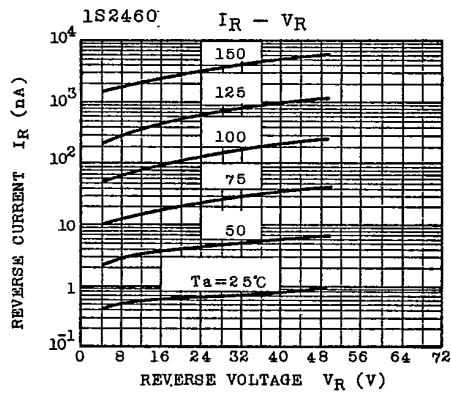
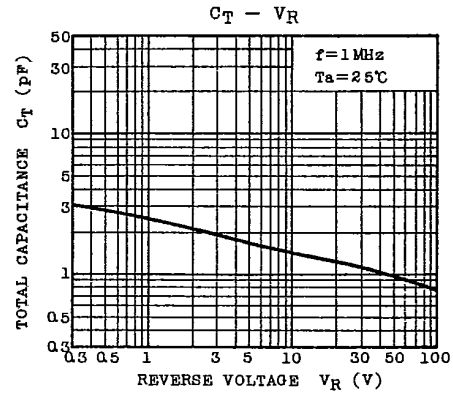
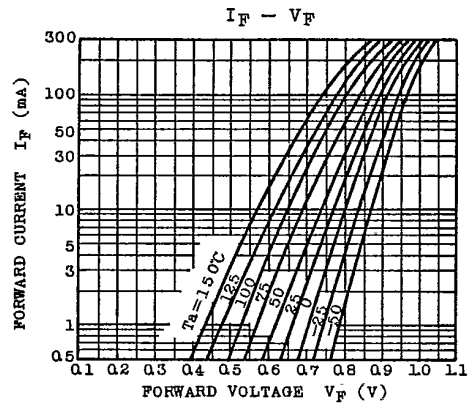
TOSHIBA CORPORATION

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